



# NPN SILICON PLANAR EPITAXIAL AMPLIFIER TRANSISTORS



BC183, BC183A, BC183B, BC183C

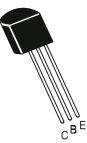
TO-92 Plastic Package

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector -Emitter Voltage	V <sub>CEO</sub>	30	V
Collector -Base Voltage	V <sub>CBO</sub>	45	V
Emitter -Base Voltage	V <sub>EBO</sub>	6	V
Collector Current Continuous	I <sub>C</sub>	100	mA
Power Dissipation@ Ta=25 <sup>o</sup> C	P <sub>D</sub>	350	mW
Derate Above 25°C		2.8	mW/ºC
Power Dissipation@ Tc=25°C	P <sub>D</sub>	1	W
Derate Above 25°C		8	mW/ºC
Operating And Storage Junction	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C
Temperature Range			
THERMAL RESISTANCE			
Junction to ambient	R <sub>th(j-a)</sub>	357	°C/W
Junction to case	R <sub>th(j-c)</sub>	125	°C/W

### ELECTRICAL CHARACTERISTICS (Ta=25°C Unless Specified Otherwise)

DESCRIPTION	SYMBO	DL TEST CONDITION	MIN	TYP	MAX	UNITS
Collector -Emitter Voltage	BV <sub>CEC</sub>	<sub>D</sub> I <sub>C</sub> =2mA,I <sub>B</sub> =0	30			V
Collector -Base Voltage	BV <sub>CB0</sub>	<sub>D</sub> Ι <sub>C</sub> =10μΑ.Ι <sub>E</sub> =0	45			V
Emitter-Base Voltage	BVEB	<sub>D</sub> Ι <sub>E</sub> =100μΑ, Ι <sub>C</sub> =0	6			V
Collector-Cut off Current	I <sub>CBO</sub>	$V_{CB}=30V,I_{E}=0$		0.2	15	nA
Emitter-Cut off Current	I <sub>EBO</sub>	$V_{EB}$ =4V, $I_{C}$ =0			15	nA
DC Current Gain	h <sub>FE</sub>	$I_C=10\mu A, V_{CE}=5V$	40			
	BC183	I <sub>C</sub> =2mA,V <sub>CE</sub> =5V	120		800	
		$I_C=100mA, V_{CE}=5V^*$	80			

# NPN SILICON PLANAR EPITAXIAL AMPLIFIER TRANSISTORS



TO-92 Plastic Package

FI FCTRICAL	CHARACTERISTICS	Ta=25°C Unless	Specified Otherwise)	
LECONICAE				

DESCRIPTION	SYMBOL	. TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Emitter Saturation Voltage	V <sub>CE(Sat)</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0.5mA		0.07	0.25	V
		I <sub>C</sub> =100mA,I <sub>B</sub> =5.0mA*		0.2	0.6	V
Base Emitter Saturation Voltage	V <sub>BE(Sat)</sub>	I <sub>C</sub> =100mA,I <sub>B</sub> =5mA*			1.2	V
Base Emitter On Voltage	V <sub>BE(On)</sub>	I <sub>C</sub> =2mA,V <sub>CE</sub> =5V	0.55	0.62	0.7	V
		I <sub>C</sub> =100mA,V <sub>CE</sub> =5V*		0.83		V
		$I_C$ =100 $\mu$ A, $V_{CE}$ =5V		0.5		V

#### ELECTRICAL CHARACTERISTICS (Ta=25°C Unless Otherwise Specified)

DESCRIPTION	SYMBOL	. TEST CONDITION	MIN	MAX	UNITS	
DYNAMIC CHARACTERISTICS						
Current Gain Bandwidth Product	f <sub>T</sub>	I <sub>C</sub> =0.5mA, V <sub>CE</sub> =3V		120		MHz
		f=100MHz				
		I <sub>C</sub> =10mA, V <sub>CE</sub> =5V	150	240		MHz
		f=100MHz				
Out-Put Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>C</sub> =0			5.0	pF
		f=1MHz				
Input Capacitance	C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0		8.0		pF
		f=1MHz				
Small Signal Current Gain						
BC183	h <sub>fe</sub>	I <sub>C</sub> =2mA, V <sub>CE</sub> =5V	125		900	
		f = 1kHz				
BC183A			125		260	
BC183B			240		500	
BC183C			450		900	
Noise Figure	NF	I <sub>C</sub> =0.2mA, V <sub>CE</sub> =5V		2.0	10	dB
		Rs=2kΩ, f=1kHZ				
		F=200Hz				
*Pulse Condition: =300us, Duty Cycle=2.	0%					

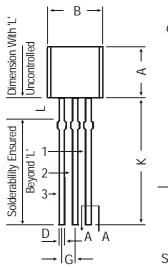
## BC183, BC183A, BC183B, BC183C

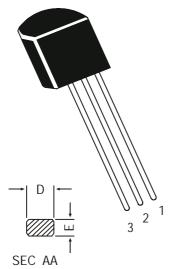
# **TO-92 Plastic Package**

33

Flat Side of Transistor and Adhesive Tape Visible 2000 pcs./Ammo Pack

# **TO-92 Plastic Package**





MIN.

4.32

4.45

3.18

0.41

0.35

1.14

1.14

12.70

All diminsions in mm.

1.982

5 DEG

MAX.

5.33

5.20

4.19

0.55

0.50

1.40

1.53

\_

2.082

DIM

А

В

С

D

Ε

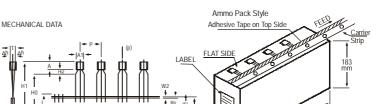
F

G

Н

Κ

L



#### **TO-92 Transistors on Tape and Ammo Pack**

### All dimensions in mm unless specified otherwise

			SPECIF	ICATIO	N	
ITEM	SYMBOL	MIN.	NOM.	MAX.	TOL .	REMARKS
BODY WIDTH	A1	4.0		4.8		
BODY HEIGHT	A	4.8		5.2		
BODY THICKNESS PITCH OF COMPONENT	T P	3.9	12.7	4.2	±1	
FEED HOLE PITCH	Po		12.7		±0.3	CUMULATIVE PITCH
FEED HOLE CENTRE TO						ERROR 1.0 mm/20 PITCH
COMPONENT CENTRE	P2		6.35		±0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER	-		F 00		+0.6	
LEADS COMPONENT ALIGNMENT	F ∆h		5.08 0	1	-0.2	AT TOP OF BODY
TAPE WIDTH	W		18		±0.5	AT TOP OF DODT
HOLD-DOWN TAPE WIDTH	Wo		6		±0.2	
HOLE POSITION	W1		9		+0.7 -0.5	
HOLD-DOWN TAPE POSITION	W2		0.5		±0.2	
LEAD WIRE CLINCH HEIGHT	Ho		16		±0.5	
COMPONENT HEIGHT	H1			23.25		
LENGTH OF SNIPPED LEADS FFFD HOLF DIAMFTFR	L		4	11.0		
TOTAL TAPE THICKNESS	Do t		4	1.2	±0.2	t1 0.3 - 0.6
LEAD - TO - LEAD DISTANCEF1,	F2		2.54	1.2	+0.4	10.5 0.0
CLINCH HEIGHT	H2			3	-0.1	
PULL - OUT FORCE	(P)	6N				

NOTES

MAXIMUM ALIGNMENT DEVIATION BETWEEN LEADS NOT TO BE GREATER THAN 0.2 mm. MAXIMUM NON-CUMULATIVE VARIATION BETWEEN TAPE FEED HOLES SHALL NOT EXCEED 1 mm IN 20 PITCHES. 1

HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO 3

HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO EXPOSURE OF ADHESIVE. NO MORE THAN 3 CONSECUTIVE MISSING COMPONENTS ARE PERMITTED. A TAPE TRAILER, HAVING AT LEAST THREE FEED HOLES ARE REQUIRED AFTER THE LAST COMPONENT. SPLICES SHALL NOT INTERFERE WITH THE SPROCKET FEED HOLES. 4 5. 6.

# Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-92 Bulk	1K/polybag	5	3" x 7.5" x 7.5"		17" x 15" x 13.5"	80K	23 kgs
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2K	17" x 15" x 13.5"	32K	12.5 kgs

Ξí C

**PIN CONFIGURATION** 

EMITTER 1.

- 2. BASE
- 3. COLLECTOR

### BC183, BC183A, BC183B, BC183C

TO-92 Plastic Package

## Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of Continental Device India Limited C-120 Naraina Industrial Area, New Delhi 110 028, India. Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290 e-mail sales@cdil.com www.cdil.com

Data Sheet